

ABSTRACT

An object of the present invention is to provide a negative electrode which attains excellent Ohmic contact
5 with an n-type gallium nitride-based compound semiconductor layer, which resists deterioration in characteristics which would be caused by heating, and which can be produced at high efficiency. Another object of the invention is to provide a gallium nitride-based
10 compound semiconductor light-emitting device having the negative electrode.

The inventive gallium nitride-based compound
semiconductor light-emitting device comprises an n-type
semiconductor layer of a gallium nitride-based compound
15 semiconductor, a light-emitting layer of a gallium nitride-based compound semiconductor and a p-type semiconductor layer of a gallium nitride-based compound semiconductor formed on a substrate in this order, and has a negative electrode and a positive electrode
20 provided on the n-type semiconductor layer and the p-type semiconductor layer, respectively; wherein the negative electrode comprises a bonding pad layer and a contact metal layer which is in contact with the n-type semiconductor layer, and the contact metal layer is
25 composed of a Cr-Al alloy.